

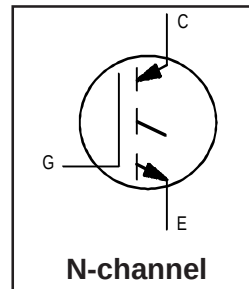
IRG4BAC50S

INSULATED GATE BIPOLAR TRANSISTOR

Standard Speed IGBT

Features

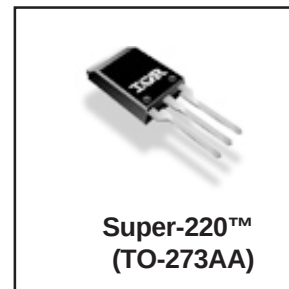
- Standard: Optimized for minimum saturation voltage and low operating frequencies (< 1kHz)
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry Super-220™ (TO-273AA) package



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 1.28V$
@ $V_{GE} = 15V, I_C = 41A$

Benefits

- Generation 4 IGBT offers highest efficiency
- Optimized for specific application conditions



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	70	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	41	
I_{CM}	Pulsed Collector Current ①	140	
I_{LM}	Clamped Inductive Load Current ②	140	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	20	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	$^\circ C$
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.64	$^\circ C/W$
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	—	40	
Wt	Weight	TBD	—	g (oz)

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.75	—	$^\circ\text{V}/^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	1.28	1.36	V	$I_C = 41A, V_{GE} = 15V$
		—	1.62	—		$I_C = 80A$
		—	1.28	—		$I_C = 41A, T_J = 150^\circ\text{C}$
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-9.3	—	$\text{mV}/^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	17	34	—	S	$V_{CE} = 100V, I_C = 41A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$
		—	—	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		—	—	1000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	180	280	nC	$I_C = 41A$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	24	37		$V_{CC} = 400V$
Q_{gc}	Gate - Collector Charge (turn-on)	—	61	92		$V_{GE} = 15V$
$t_{d(on)}$	Turn-On Delay Time	—	33	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 41A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail"
t_r	Rise Time	—	30	—		
$t_{d(off)}$	Turn-Off Delay Time	—	650	980		
t_f	Fall Time	—	400	600	mJ	See Fig. 9, 10, 14
E_{on}	Turn-On Switching Loss	—	0.72	—		
E_{off}	Turn-Off Switching Loss	—	8.27	—		
E_{ts}	Total Switching Loss	—	8.99	13	ns	$T_J = 150^\circ\text{C}$, $I_C = 41A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail"
$t_{d(on)}$	Turn-On Delay Time	—	31	—		
t_r	Rise Time	—	31	—		
$t_{d(off)}$	Turn-Off Delay Time	—	1080	—	mJ	See Fig. 11, 14
t_f	Fall Time	—	620	—		
E_{ts}	Total Switching Loss	—	15	—		
L_C	Internal Collector Inductance	—	2.0	—	nH	Measured 5mm from package
L_E	Internal Emitter Inductance	—	5.0	—		
C_{ies}	Input Capacitance	—	4100	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$
C_{oes}	Output Capacitance	—	250	—		
C_{res}	Reverse Transfer Capacitance	—	48	—		

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See Fig. 13b)
- ② $V_{CC} = 80\%(V_{CES})$, $V_{GE} = 20V$, $L = 10\mu H$, $R_G = 5.0\Omega$, (See Fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.

- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

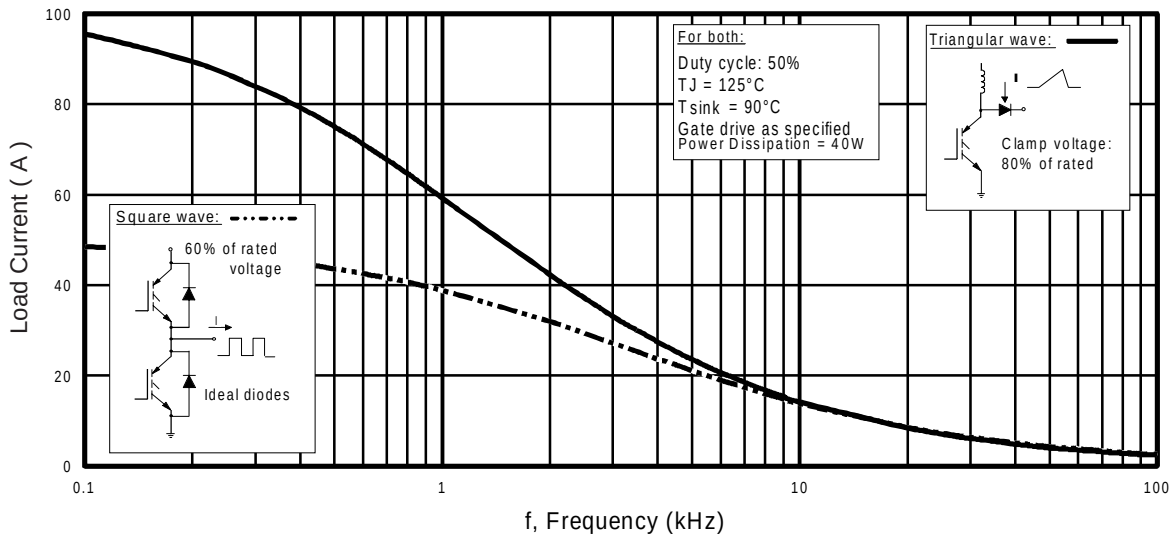


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

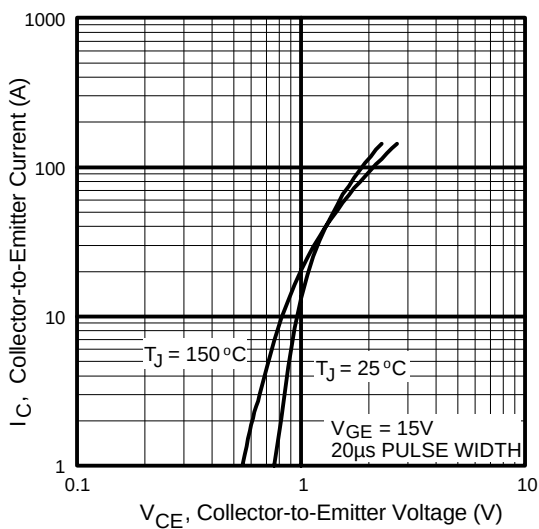


Fig. 2 - Typical Output Characteristics

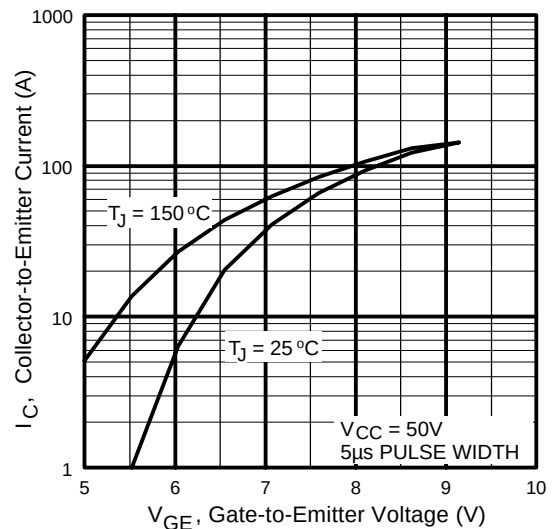


Fig. 3 - Typical Transfer Characteristics

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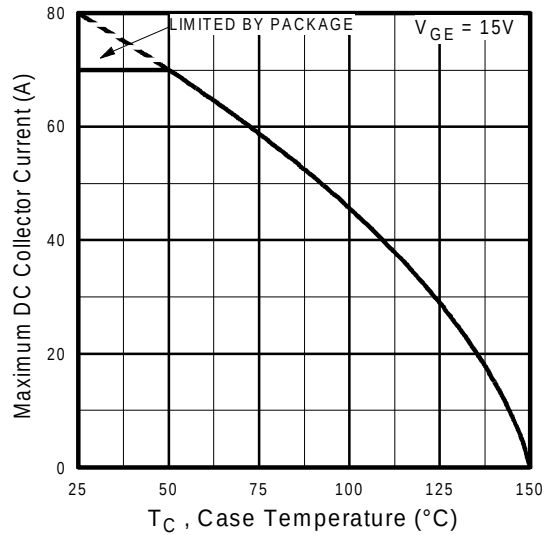


Fig. 4 - Maximum Collector Current vs. Case Temperature

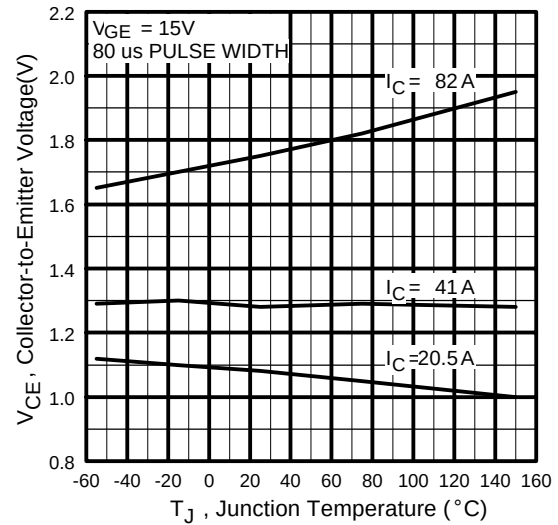


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

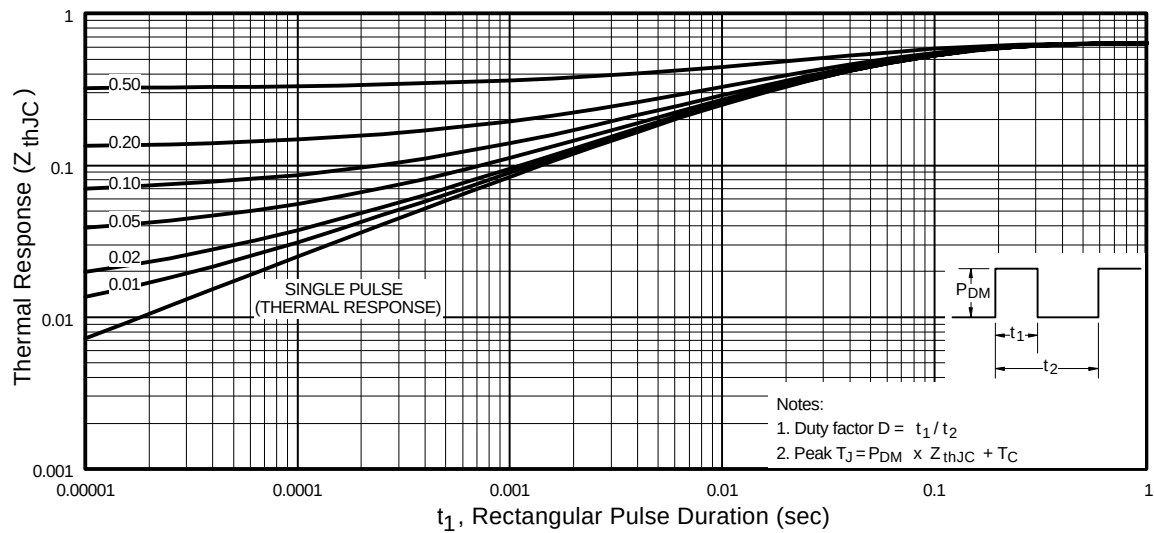


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

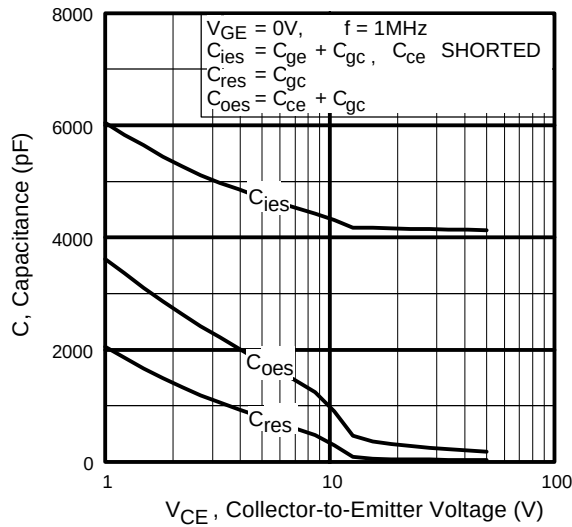


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

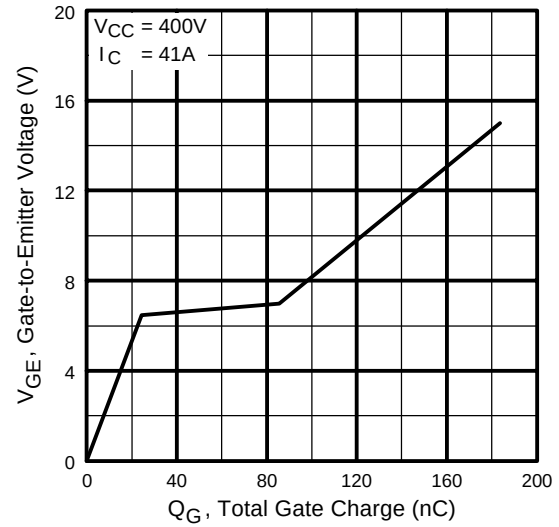


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

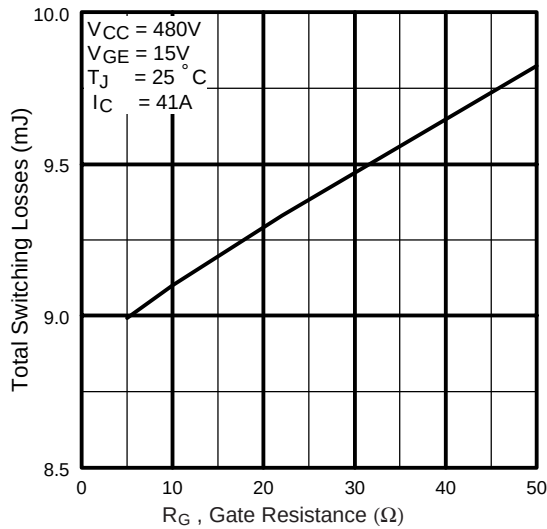


Fig. 9 - Typical Switching Losses vs. Gate Resistance

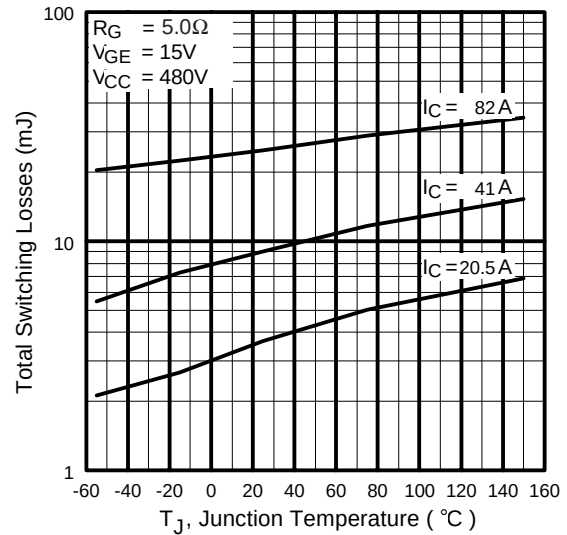


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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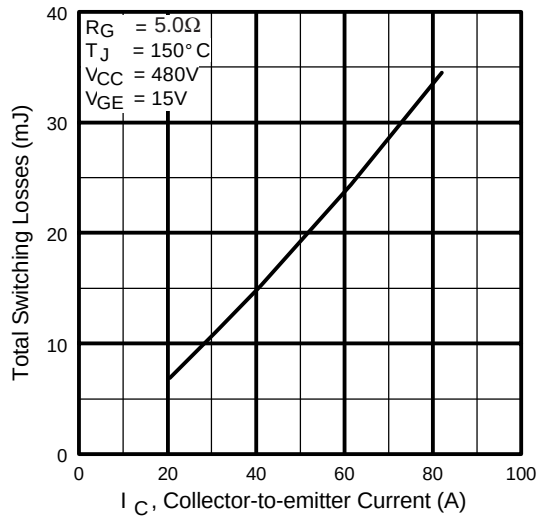


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

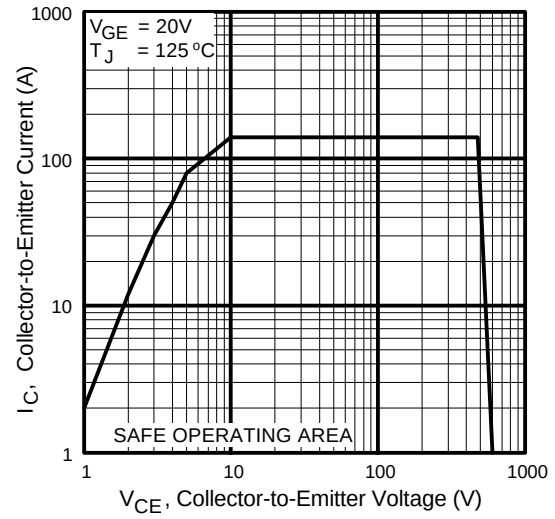


Fig. 12 - Turn-Off SOA

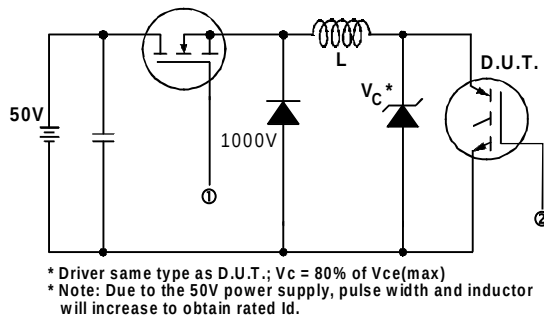


Fig. 13a - Clamped Inductive Load Test Circuit

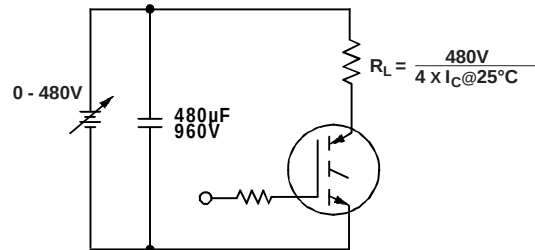


Fig. 13b - Pulsed Collector Current Test Circuit

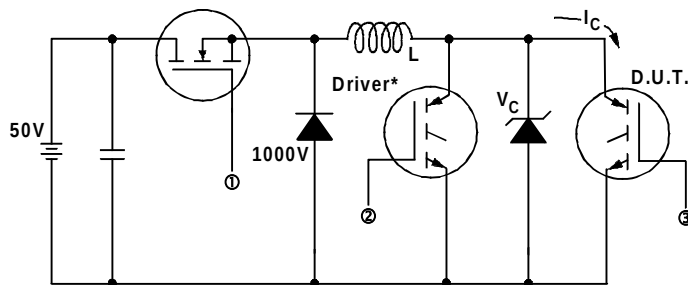


Fig. 14a - Switching Loss Test Circuit

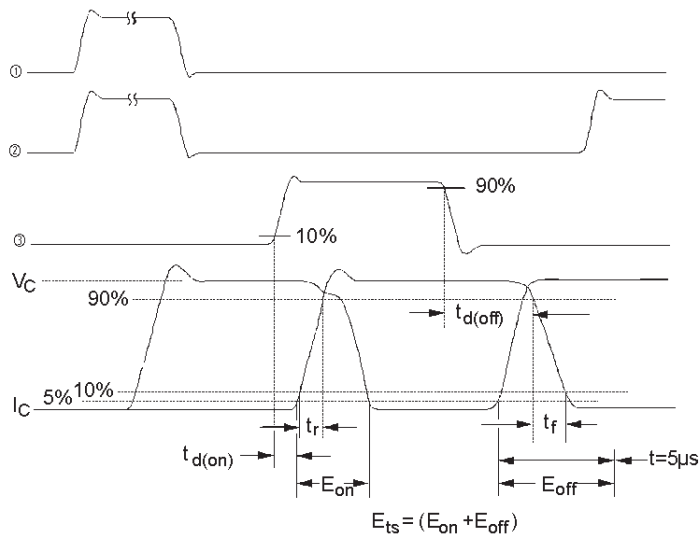
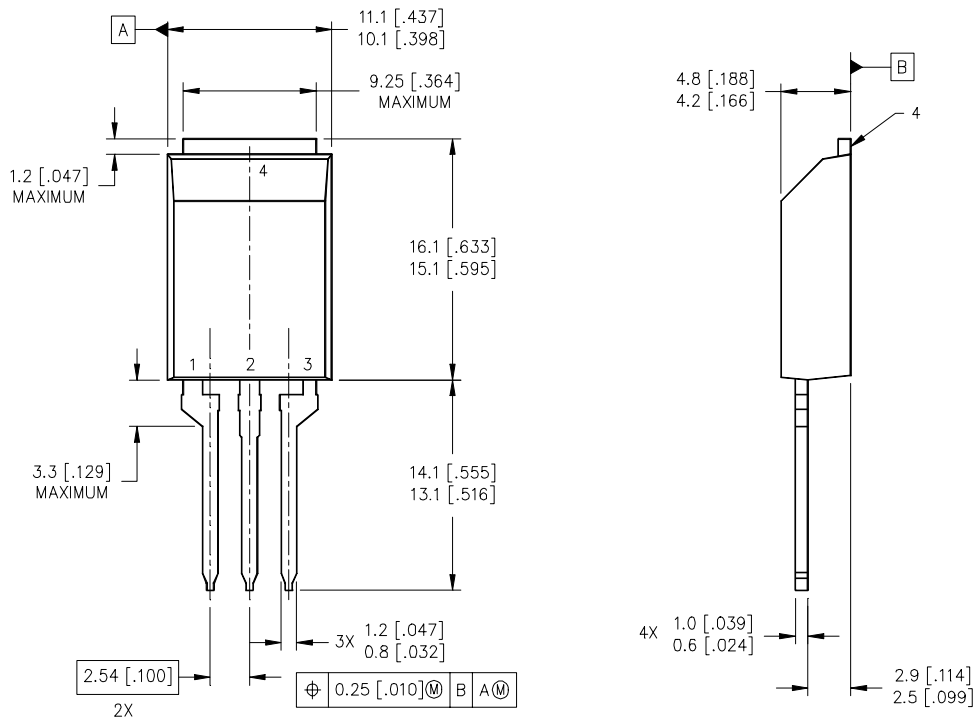


Fig. 14b - Switching Loss Waveforms

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Super-220™ (TO-273AA) Package Outline



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-273AA.

LEAD ASSIGNMENTS

MOSFET	IGBT
1 – GATE	1 – GATE
2 – DRAIN	2 – COLLECTOR
3 – SOURCE	3 – EMITTER
4 – DRAIN	4 – COLLECTOR

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Data and specifications subject to change without notice. 1/2000